MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK099V65Z

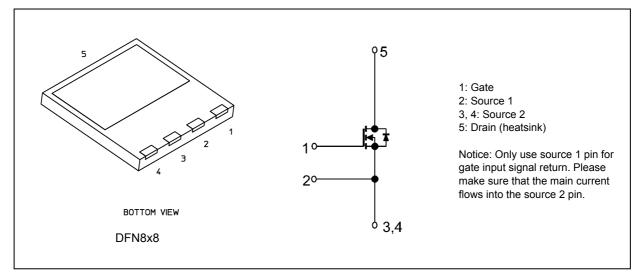
1. Applications

Switching Power Supplies

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.08 \Omega$ (typ.)
- (2)High-speed switching properties with the lower capacitance.
- Enhancement mode: V_{th} = 3 to 4 V (V_{DS} = 10 V, I_{D} = 1.27 mA) (3)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	650	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	30	A
Drain current (pulsed)	(Note 1)	I _{DP}	120]
Power dissipation (T _c =	= 25 °C)	PD	230	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	265	mJ
Single-pulse avalanche current		I _{AS}	7.5	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	30]
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	120	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

> Start of commercial production 2019-06 2019-09-27

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.543	°C/W

Note 1: Ensure that the channel temperature does not exceed 150 °C. Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 8.34 mH, I_{AS} = 7.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V_{DS} = 650 V, V_{GS} = 0 V	_	_	2	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	650	_	_	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1.27 mA	3	_	4	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 15 A		0.08	0.099	Ω

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V_{DS} = 300 V, V_{GS} = 0 V, f = 100 kHz		2780	_	pF
Reverse transfer capacitance	C _{rss}			2	_	
Output capacitance	C _{oss}			63		
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V	_	116	_	pF
Gate resistance	r _g	V _{DS} = OPEN , f = 1 MHz		3	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1		20	_	ns
Switching time (turn-on time)	t _{on}		_	50	_	
Switching time (fall time)	t _f			4	_	
Switching time (turn-off time)	t _{off}			100		ns
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \leq V_{(BR)DSS}, I_D \leq 15 \text{ A}$	120	_	_	V/ns

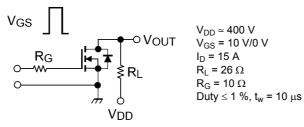


Fig. 6.2.1 Switching Time Test Circuit

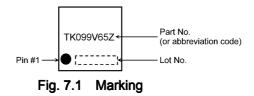
6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 10 V, I _D = 30 A		47	_	nC
Gate-source charge 1	Q _{gs1}		_	15	_	
Gate-drain charge	Q _{gd}		_	12	_	

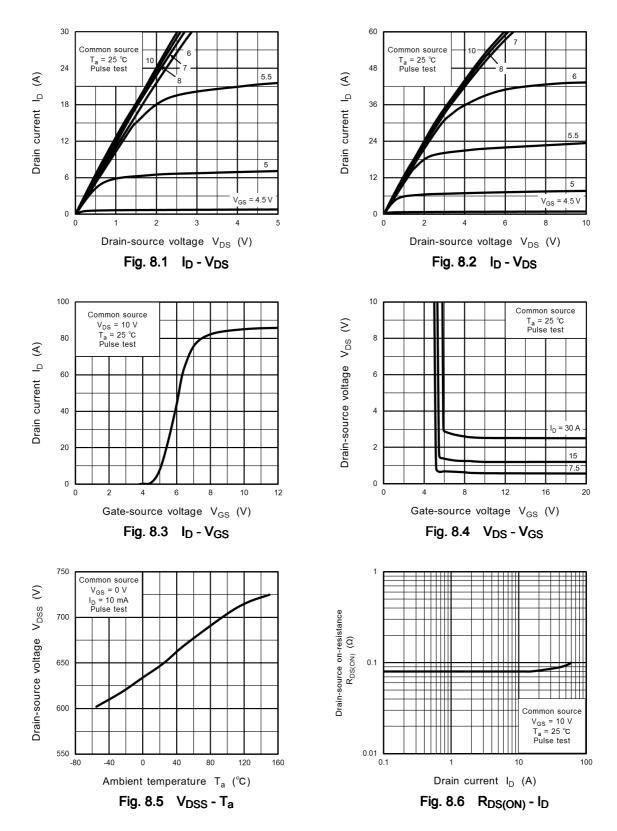
6.4. Source-Drain Characteristics ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V_{DSF}	I _{DR} = 30 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	V _{DD} = 400 V,		330	_	ns
Reverse recovery charge	Q _{rr}	I _{DR} = 15 A, V _{GS} = 0 V -dI _{DR} /dt = 100 A/μs	—	5.1	_	μC
Peak reverse recovery current	l _{rr}		—	31	—	А
Diode dv/dt ruggedness	dv/dt	$V_{DD} \leq 400$ V, $I_{DR} \leq 15$ A, V_{GS} = 0 V	50	_	_	V/ns

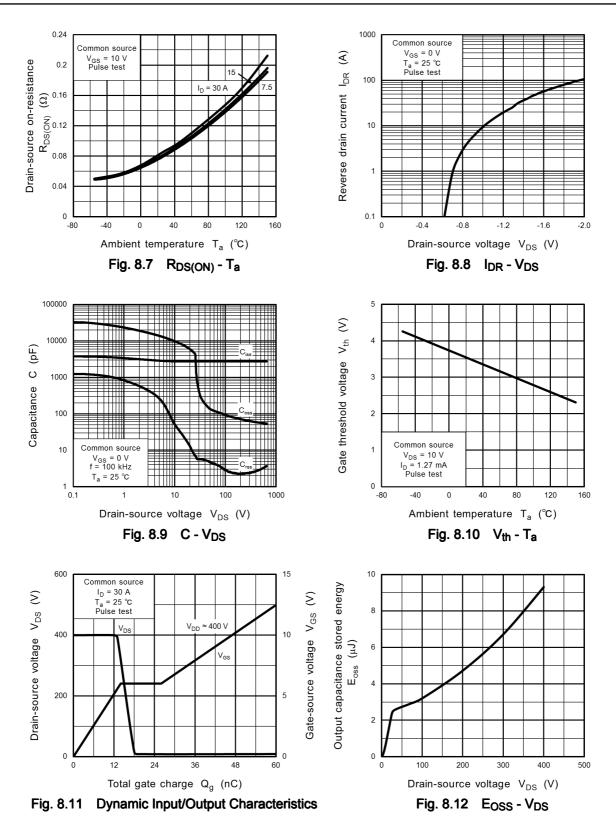
7. Marking

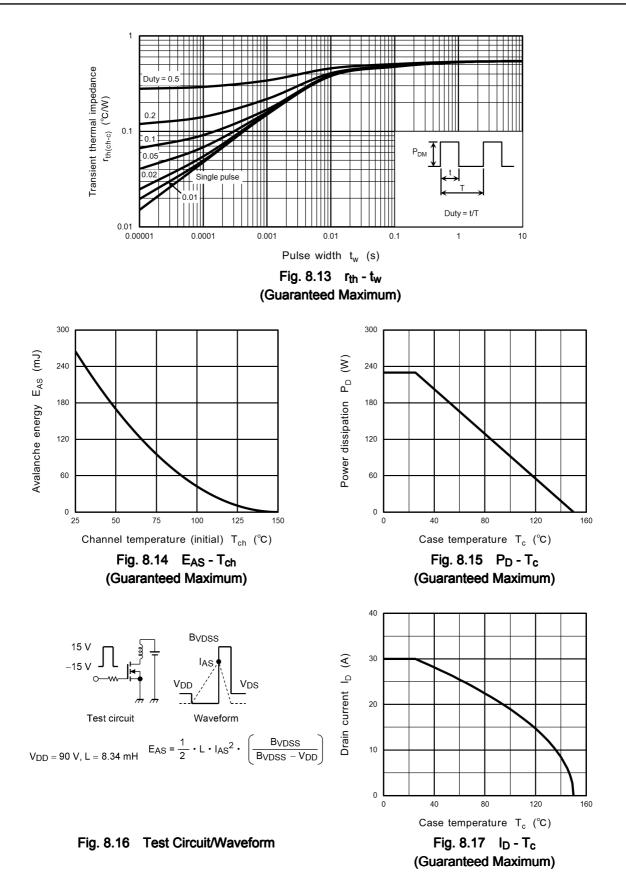


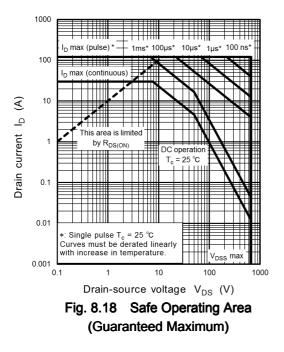
8. Characteristics Curves (Note)











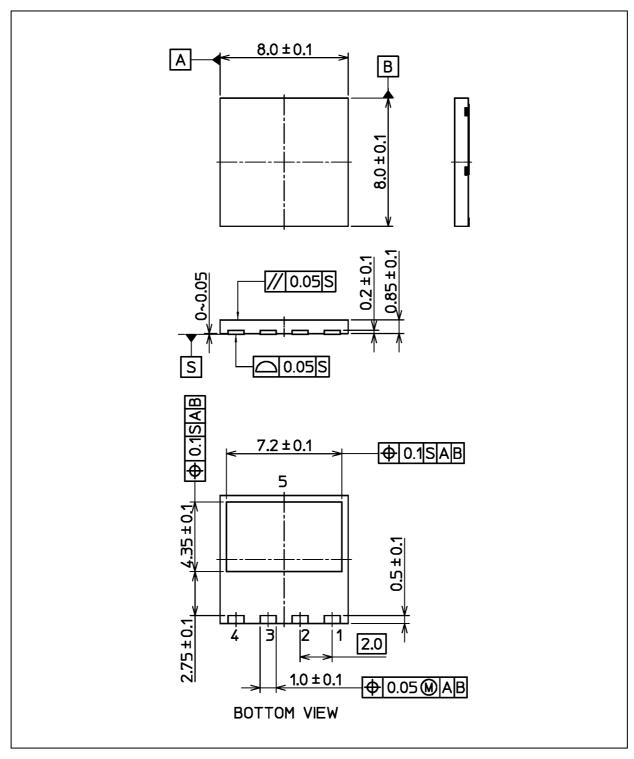
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TK099V65Z

Package Dimensions

Unit: mm



Weight: 0.175 g (typ.)

	Package Name(s)
TOSHIBA: 2-8T1A	
Nickname: DFN8x8	

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